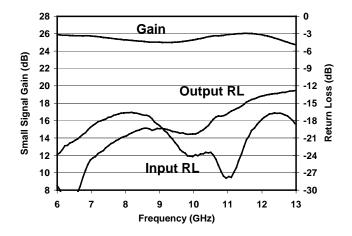


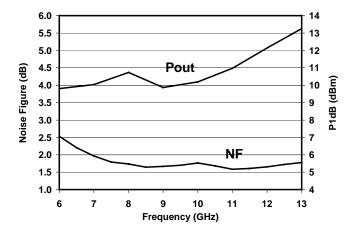
6-13 GHz Low Noise Amplifier TGA8399B-EPU

Key Features and Performance

- 3 Stage LNA 0.25um pHEMT Technology
- 6-13 GHz Frequency Range
- 1.75 dB Typical Noise Figure Midband
- 25 dB Nominal Gain
- High Input Power Handling: ~ 20dBm
- Balanced Input for Low VSWR
- 5V @ 65mA Self Bias



Typical Measured Small Signal Gain & RL

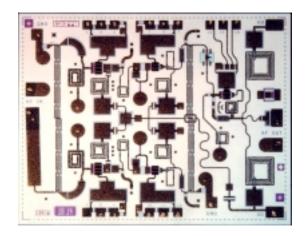


Primary Applications

Point-to-Point Radio

Release Status

 Engineering Prototype Unit (EPU) samples available

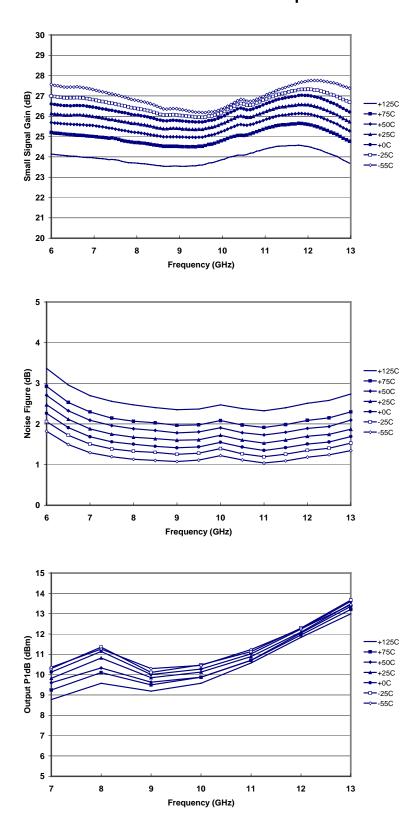


Chip Dimensions 3.07mm x2.41mm x 0.152mm

Typical Measured NF and Pout

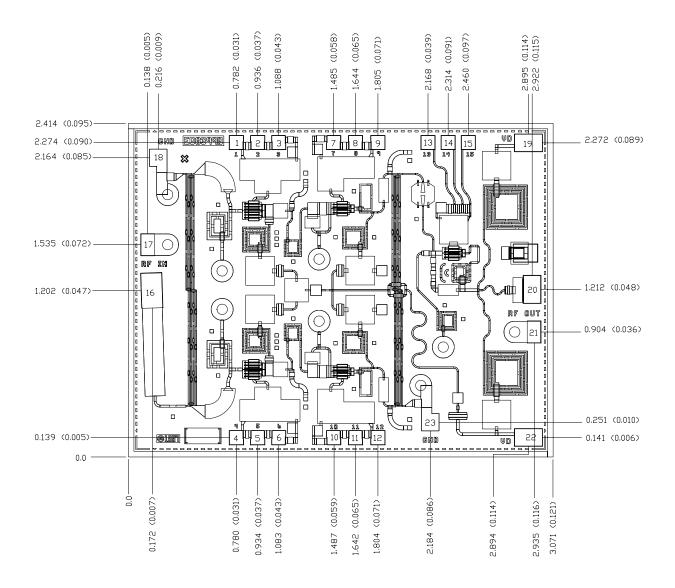


TA8399B Performance vs Temperature



Advance Product Information





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Units: millimeters (inches)
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Thickness: 0.1524 (0.006) (reference only)

Chip edge to bond pad dimensions are shown to center of bond pad

Chip size tolerance: +/- 0.051 (0.002)

```
Bond Pad #1~#15 (R1~R15)
                                        0.100 \times 0.100 (0.004 \times 0.004)
Bond Pad #16 (RF Input)
                                        0.152 \times 0.252 (0.006 \times 0.010)
Bond Pad #17 (GND)
                                        0.100 \times 0.161 (0.004 \times 0.006)
Bond Pad #18 (GND)
                                        0.125 \times 0.128 (0.005 \times 0.005)
Bond Pad #19 (VD)
                                        0.125 \times 0.200 (0.005 \times 0.008)
Bond Pad #20 (RF Dutput)
                                        0.125 \times 0.200 (0.005 \times 0.008)
Bond Pad #21 (GND)
                                        0.100 \times 0.161 (0.004 \times 0.006)
Bond Pad #22 (VD)
                                        0.125 \times 0.200 (0.005 \times 0.008)
Bond Pad #23 (GND)
                                        0.125 \times 0.128 (0.005 \times 0.005)
```



Recommended Assembly Layout

